

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-7. (Canceled)

8. (Currently Amended) A structure formed in a substrate of monolithic semiconductor material, the structure comprising:

at least one trench formed in the substrate, the at least one trench having an open top and an open bottom, and a coating on the lateral walls of the at least one trench with material resistant to etching;

a cavity having walls formed below each at least one trench and in communication with the open bottom of the at least one trench, and a coating on the walls of the cavity with material inhibiting epitaxial growth; and

an epitaxial layer formed on the substrate to cover the open top of the at least one trench and to encase the at least one trench and the cavity in the substrate.

9. (Original) The structure of claim 8, comprising a plurality of trench and cavity pairs formed in the substrate.

10. (Original) The structure of claim 9, wherein each trench and cavity pair are formed at different levels within the substrate.

11. (Original) The structure of claim 9, wherein each trench and cavity pair are formed to have different cross-sectional configurations.

12. (Original) The structure of claim 9, wherein each trench and cavity pair are formed to have different cross-sectional sizes.

13. (Original) The structure of claim 9, wherein each trench and cavity pair are formed to have a different cross-sectional size and to be formed at different levels in the substrate.

14. (Canceled)

15. (Currently Amended) A monolithic wafer of semiconductor material, comprising:

a plurality of buried cavities formed in and completely surrounded by the semiconductor material, each cavity of the plurality of buried cavities coated with having only one coating on at least one wall thereof consisting of a layer of material inhibiting epitaxial growth.

16. (Original) The wafer of claim 15, wherein each cavity of the plurality of buried cavities are formed parallel to one another and at a right angle with respect to a drawing plane of the semiconductor material.

17. (Original) The wafer of claim 16, wherein the plurality of cavities are formed at the same height.

18. (Original) The wafer of claim 16, wherein each of the cavities of the plurality of cavities are formed at a different level in the semiconductor material.

19. (Currently Amended) A structure formed in monolithic semiconductor material, the structure comprising:

a cavity formed in the monolithic semiconductor material and having an open top, the cavity having at least one wall with a single coating on the at least one wall that is formed of a layer of material inhibiting epitaxial growth; and

a membrane formed of epitaxial growth on the monolithic semiconductor material that covers the open top of the cavity in the substrate, the membrane having a thickness in the range of between 1 and 3 μm .

20. (Canceled)

21. (Previously Presented) The structure of claim 19, further comprising at least one trench etched into the membrane and of a depth to be in communication with the cavity.

22.-23. (Canceled)

24. (Currently Amended) The wafer of claim-14_9, wherein the material inhibiting epitaxial growth comprises TEOS.

25. (Currently Amended) The wafer of claim-14_9, wherein the material inhibiting epitaxial growth comprises oxide.

26. (Currently Amended) The wafer of claim-14_9, wherein the material inhibiting epitaxial growth comprises nitride.

27. (Currently Amended) The wafer of claim-14_9, further comprising a plurality of buried channels adjacent and separated from each other by dividers.

28. (Currently Amended) A wafer of monolithic monocrystalline semiconductor material, comprising at least one-a plurality of buried cavities, each cavity completely surrounded by said monolithic monocrystalline material and each cavity having walls covered with a single coating formed of a layer of material inhibiting epitaxial growth, - and a-the plurality of buried channels cavities positioned adjacent to and separated from each other by dividers.

29. (Previously Presented) The wafer of claim 28, wherein the material inhibiting epitaxial growth comprises oxide.

30. (Previously Presented) The wafer of claim 28, wherein the material inhibiting epitaxial growth comprises TEOS.

31. (Previously Presented) The wafer of 28, wherein the material inhibiting epitaxial growth comprises nitride.

32. (Currently Amended) A monolithic wafer of monocrystalline semiconductor material, comprising at least one-a plurality of buried cavities, each cavity completely surrounded by said monocrystalline material and having walls that are covered with a single coating that is formed of a layer of material inhibiting epitaxial growth, and a-the plurality of buried cavities positioned at different heights within the wafer of monocrystalline semiconductor material.

33. (Previously Presented) The wafer of claim 32, wherein the material inhibiting epitaxial growth comprises oxide.

34. (Previously Presented) The wafer of claim 32, wherein the material inhibiting epitaxial growth comprises TEOS.

35. (Previously Presented) The wafer of 32, wherein the material inhibiting epitaxial growth comprises nitride.